

WHAT IS CLAIMED IS:

Sub
A1 7

1. A semiconductor device comprising:
a filmy resinous substrate;
a resinous layer provided on said filmy resinous substrate; and
a semiconductor layer comprising silicon provided over said resinous layer.

Sub
EP

2. The device of claim 1 wherein said semiconductor layer constitutes an inverted-staggered thin-film transistor.

3. The device of claim 1 wherein said substrate comprises a material selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite and polyimide.

Sub
B1

4. The device of claim 1 wherein said resinous layer comprises a material selected from the group consisting of methyl ester of acrylic acid, ethyl ester of acrylic acid, butyl ester of acrylic acid, 2-ethylhexyl ester of acrylic acid.

Sub
A2 7

5. A semiconductor device comprising:
a filmy resinous substrate;
a resinous layer provided on said filmy resinous substrate; and
a thin film transistor comprising a semiconductor layer comprising silicon on said resinous layer;
an interlayer dielectric layer comprising a resinous material provided over said semiconductor layer; and

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an indium tin oxide layer provided on said interlayer dielectric layer.

Sub E4
6. The device of claim 5 wherein said substrate comprises a material selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite and polyimide.

Sub B3
7. The device of claim 5 wherein said resinous layer comprises a material selected from the group consisting of methyl ester of acrylic acid, ethyl ester of acrylic acid, butyl ester of acrylic acid, 2-ethylhexyl ester of acrylic acid.

Sub C3
8. The device of claim 5 wherein said interlayer dielectric layer comprises polyimide.

9. A semiconductor device comprising:
a filmy resinous substrate;
a resinous layer provided on said filmy resinous substrate; and
a semiconductor layer comprising silicon provided over said resinous layer,

wherein said substrate comprises a material selected from the group consisting of polyethylene terephthalate, polyethylene naphthalate, polyethylene sulfite and polyimide.

10. The device of claim 9 wherein said resinous layer comprises a material selected from the group consisting of methyl ester of acrylic acid, ethyl ester of acrylic acid, butyl ester of acrylic acid, 2-ethylhexyl ester of acrylic acid.

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